

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1234	capacitor and (HSG or (Hemispherical adj grain))	USPAT; EPO; JPO; DERWEN T; IBM TDB	2001/11/18 09:05
2	BRS \ v	L2	107277 9	semiconductor	USPAT; EPO; JPO; DERWEN T; IBM TDB	2001/11/18 09:06
3	BRS	L3	1059	1 and 2	USPAT; EPO; JPO; DERWEN T; IBM TDB	2001/11/18 09:06
4	BRS	L4	790	3 and ((polysilicon or polycrystal\$) and (open\$ or window or hole or via or trench))	USPAT; EPO; JPO; DERWEN T; IBM TDB	2001/11/18 09:17
5	BRS	L7	768	4 and ((inner adj surface) or (outer adj surface) or dielectrice or rugg\$ or polysilicon or undop\$ orseed or chemisorb\$ or precursor or monolayer)	USPAT; EPO; JPO; DERWEN T; IBM TDB	2001/11/18 09:27
6	BRS	L9	66	"5142438"	USPAT; EPO; JPO; DERWEN T; IBM TDB	2001/11/18 10:01

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L10	27	"5362632"	USPAT; EPO; JPO; DERWEN T; IBM TDB	2001/11/18 10:01
8	BRS	L8	601	7 and (TaO or ZrO or WO or AlO or HfO or monolayer or side or bottom)	USPAT; EPO; JPO; DERWEN T; IBM TDB	2001/11/18 10:05